

**Amendments to the Specification:**

**Please amend paragraph [0001] as follows:**

[0001] This application claims the priority benefit of Taiwan application serial no. 92120050, filed ~~Jul,~~ July 23, 2003. This application is ~~related to a continuation-in-part of application Ser. No. 10/445,558, filed on May 27, 2003, which is a continuation-in-part of U.S. Pat. No. 6,897,507, to Ser. No. 10/303,451, filed on Nov. 25, 2002, which is a continuation of to~~ U.S. Pat. No. 6,489,647, filed on ~~May.~~ May 28, 2002, which is a division of to U.S. Pat. No. 6,455,885, filed on Oct. 03, 2001, which is a division of to U.S. Pat. No. 6,303,423, filed on Nov. 27, 2000, which is a continuation-in-part of application to Ser. No. 09/637,926, filed on Aug. 14, 2000, which is a continuation-in-part of to U.S. Pat. No. 6,383,916, filed on Feb. 17, 1999, which is a continuation-in-part of application and to Ser. No. 09/216,791, filed on Dec. 21, 1998.

**Please amend paragraph [0025] as follows:**

[0025] Afterwards, a passivation layer 126 ~~140~~ is formed over the dielectric layers 122 and 124 and the circuit layers 132 and 134, covering the electrode 152 and the electromagnetic-field shielding layer 160. The passivation layer 126 ~~150~~ has a thickness t, for example, larger than 0.35 microns. It should be noted that the passivation layer 126 ~~150~~ should be thick enough to prevent moisture, impurities, mobile ions or transitional metal elements from penetrating therethrough. The passivation layer 126 ~~140~~ has openings 128 and 129 exposing the electrode 152 and the circuit layer 134. The openings 129 have a width, for example, ranging from 0.1 microns to 20 microns. The passivation layer 126 ~~150~~ can be a silicon-dioxide layer, a silicon-nitride layer, a phosphosilicate-glass (PSG) layer, a silicon oxynitride layer or a composite structure by depositing some or all of the above-mentioned dielectric layers.